

TLE9350VSJ

High speed CAN FD transceiver







Features

- Fully compliant to ISO 11898-2:2016 and SAE J2284-4/-5
- Loop delay symmetry for CAN FD data frames up to 5 MBit/s
- Certified according to VeLIO (Vehicle LAN Interoperability and Optimization) test requirements
- Very low electromagnetic emission (EME) allows the use without additional common mode choke
- V_{10} input for voltage adaption to the microcontroller interface (3.3 V or 5 V)
- Excellent ESD robustness
- TxD time-out function
- Very low CAN bus leakage current in power-down state
- Overtemperature protection
- Protected against automotive transients according to ISO 7637 and SAE J2962-2
- · Power-save mode
- Green Product (RoHS compliant)

Potential applications

- Engine control units (ECU)
- Electric power steering
- Transmission control units (TCUs)
- Chassis control modules

Product validation

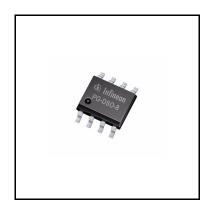
Qualified for automotive applications. Product validation according to AEC-Q100.

Description

The TLE9350VSJ is a high speed CAN transceiver, used in HS CAN systems for automotive applications as well as for industrial applications. It is designed to fulfill the requirements of ISO 11898-2:2016 physical layer specification as well as SAE J1939 and SAE J2284.

The TLE9350VSJ is available in a RoHS compliant, halogen free PG-DSO-8 package.

As an interface between the physical bus layer and the HS CAN protocol controller, the TLE9350VSJ is designed to protect the microcontroller against interferences generated inside the network. A very high ESD





robustness and the optimized RF immunity allows the use in automotive applications without additional protection devices, such as suppressor diodes or common mode chokes.

Based on the high symmetry of the CANH and CANL output signals, the TLE9350VSJ provides a very low level of electromagnetic emission (EME) within a wide frequency range. The TLE9350VSJ fulfills even stringent EMC test limits without an additional external circuit, such as a common mode choke.

The optimized transmitter symmetry combined with the optimized delay symmetry of the receiver enables the TLE9350VSJ to support CAN FD data frames. The device supports data transmission rates up to 5 MBit/s, depending on the size of the network and the inherent parasitic effects.

Fail-safe features, such as overtemperature protection, output current limitation or the TxD time-out feature are designed to protect the TLE9350VSJ and the external circuitry from irreparable damage.

Туре	Package	Marking
TLE9350VSJ	PG-DSO-8	9350V



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1 Block diagram

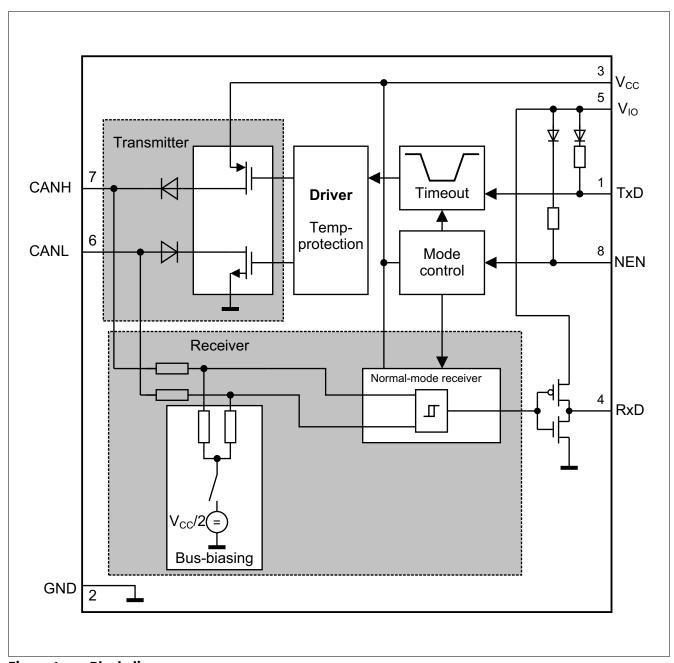


Figure 1 Block diagram



2 Pin configuration

2.1 Pin assignment

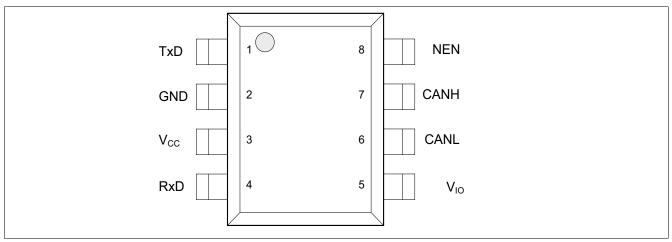


Figure 2 Pin assignment

2.2 Pin definitions

Table 1 Pin definitions and functions

Pin No.	Symbol	Function
1	TxD	Transmit data input; Internal pull-up to $V_{\rm IO}$, "low" for dominant state.
2	GND	Ground
3	V _{cc}	Transmitter supply voltage; A decoupling capacitor of 1 μ F to GND is recommended, V_{CC} can be turned off in power-save mode.
4	RxD	Receive data output; "Low" in dominant state.
5	V _{IO}	Digital supply voltage input; Adapts the logical input voltage level and output voltage level of the transceiver to the voltage level of the microcontroller supply, A 100 nF decoupling capacitor to GND is recommended.
6	CANL	CAN bus low level I/O; Bus level on the CANL input/output.
7	CANH	CAN bus high level I/O; Bus level on the CANH input/output.
8	NEN	Not enable input; Internal pull-up to $V_{\rm IO}$, "low" for normal-operating mode.



General product characteristics 3

3.1 Absolute maximum ratings

Absolute maximum ratings voltages, currents and temperatures¹⁾ Table 2

All voltages with respect to ground; positive current flowing into pin; (unless otherwise specified)

Parameter	Symbol		Value	es .	Unit		Number
		Min.	Тур.	Max.		Test Condition	
Voltages	-	.!	· ·				-
Transmitter supply voltage	V_{cc}	-0.3	_	6.0	V	_	P_7.1.1
Digital supply voltage	V _{IO}	-0.3	-	6.0	V	-	P_7.1.2
CANH and CANL DC voltage versus GND	V _{CANH}	-40	-	40	V	-	P_7.1.3
Differential voltage between CANH and CANL	V _{CAN_Diff}	-40	-	40	V	-	P_7.1.4
Voltage at the digital input pins: NEN, TxD	V _{MAX_IO}	-0.3	-	6.0	V	-	P_7.1.5
Voltage at the digital output pin: RxD	V _{MAX_RxD}	-0.3	-	V _{IO} +0.3	V	-	P_7.1.9
Currents							
RxD output current	I_{RxD}	-5	_	5	mA	_	P_7.1.6
Temperatures	1					1	
Junction temperature	T_{i}	-40	_	150	°C	_	P_7.1.7
Storage temperature	T_{S}	-55	_	150	°C	-	P_7.1.8
ESD immunity			J.			·	
ESD immunity at CANH, CANL versus GND	V _{ESD_HBM_CAN}	-10	-	10	kV	HBM; (100 pF via 1.5 kΩ) ²⁾	P_7.1.10
ESD immunity at all other pins	V _{ESD_HBM_ALL}	-2	-	2	kV	HBM; (100 pF via 1.5 kΩ) ²⁾	P_7.1.11
ESD immunity corner pins	V _{ESD_CDM_CP}	-750	_	750	V	CDM ³⁾	P_7.1.14
ESD immunity all other pins	$V_{\rm ESD_CDM_OP}$	-500	_	500	٧	CDM ³⁾	P_7.1.12

¹⁾ Not subject to production test, specified by design.

Note:

Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as outside normal-operating range. Protection functions are not designed for continuous repetitive operation.

²⁾ ESD susceptibility, Human Body Model (HBM) according to ANSI/ESDA/JEDEC JS-001.

³⁾ ESD susceptibility, Charge Device Model (CDM) according to ANSI/ESDA/JEDEC JS-002.



3.2 Functional range

Table 3 Functional range

Parameter	Symbol		Value	s	Unit	Note or Test Condition	Number
		Min.	Тур.	Max.			
Supply voltages	,						,
Transmitter supply voltage	$V_{\rm cc}$	4.75	_	5.25	V	_	P_7.2.1
Digital supply voltage	V _{IO}	3.0	_	5.5	V	_	P_7.2.2
Thermal parameters				•			
Junction temperature	T _j	-40	_	150	°C	1)	P_7.2.3

¹⁾ Not subject to production test, specified by design.

Note:

Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

3.3 Thermal resistance

Note:

This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, please visit **www.jedec.org**.

Table 4 Thermal resistance¹⁾

Parameter	Symbol		Value	s	Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
Thermal resistance		"		"			
Junction to ambient PG-DSO-8	R _{thJA_DSO8}	-	120	-	K/W	2)	P_7.3.2
Thermal shutdown (junction tem	perature)	"		"			
Thermal shutdown temperature, rising	$T_{ m JSD}$	170	180	190	°C	temperature falling: minimum 150°C	P_7.3.3
Thermal shutdown hysteresis	ΔΤ	5	10	20	K		P_7.3.4

¹⁾ Not subject to production test, specified by design.

²⁾ Specified R_{thJA} value is according to JEDEC JESD51-2,-7 at natural convection on FR4 2s2p board. The product was simulated on a 76.2 × 114.3 × 1.5 mm³ board with two inner copper layers (2 × 70 μ m Cu, 2 × 35 μ m Cu).



High speed CAN functional description 4

HS CAN is a serial bus system that connects microcontrollers, sensors and actuators for real-time control applications. ISO 11898 describes the use of the controller area network (CAN) within road vehicles. According to the 7-layer OSI reference model the physical layer of a HS CAN bus system specifies the data transmission from one CAN node to all other CAN nodes available within the network. The physical layer specification of a CAN bus system includes all electrical specifications of a CAN. The CAN transceiver is part of the physical layer specification.

4.1 High speed CAN physical layer

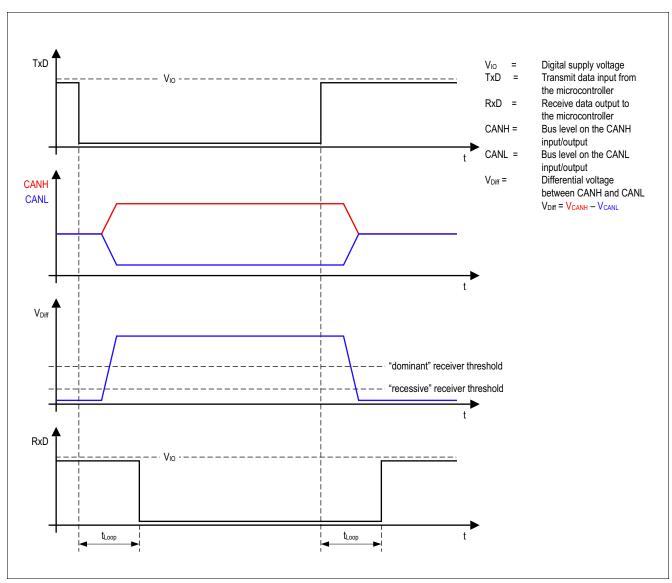


Figure 3 High speed CAN bus signals and logic signals



The TLE9350VSJ operates as an interface between the CAN controller and the physical bus medium. A HS CAN is a two wire differential network which allows data transmission rates up to 5 MBit/s. The characteristics for a HS CAN are the two signal states on the CAN bus: dominant and recessive (see **Figure 3**).

The CANH and CANL pins are the interface to the CAN bus and both pins operate as an input and output simultaneously. The RxD and TxD pins are the interface to the microcontroller. The pin TxD is the serial data input from the CAN controller, the RxD pin is the serial data output to the CAN controller. As shown in **Figure 1**, the TLE9350VSJ includes a receiver and a transmitter unit, allowing the transceiver to send data to the bus medium and monitor the data from the bus medium at the same time. The TLE9350VSJ converts the serial data stream which is available on the transmit data input TxD, into a differential output signal on the CAN bus, provided by the CANH and CANL pins. The receiver stage of the TLE9350VSJ monitors the data on the CAN bus and converts them to a serial, single-ended signal on the RxD output pin. A "low" signal on the TxD pin creates a dominant signal on the CAN bus, followed by a logical "low" signal on the RxD pin (see **Figure 3**). The feature of broadcasting data to the CAN bus and listening to the data traffic on the CAN bus simultaneously is essential to support the bit-to-bit arbitration within CAN.

ISO 11898-2:2016 specifies the voltage levels for HS CAN transceivers. Whether a data bit is dominant or recessive depends on the voltage difference between the CANH and CANL pins ($V_{Diff} = V_{CANH} - V_{CANL}$).

To transmit a dominant signal to the CAN bus the amplitude of the differential signal $V_{\rm Diff}$ is higher than or equal to 1.5 V. To receive a recessive signal from the CAN bus the amplitude of the differential $V_{\rm Diff}$ is lower than or equal to 0.5 V.

In partially-supplied high speed CAN the bus nodes of one common network have different power supply conditions. Some nodes are connected to the power supply, while other nodes are disconnected from the power supply and in power-down state. Regardless of whether the CAN bus subscriber is supplied or not, each subscriber connected to the common bus media must not interfere with the communication. The TLE9350VSJ is designed to support partially-supplied networks. In power-down state, the receiver input resistors are switched off and the transceiver input has a high resistance.

For permanently supplied ECUs, the HS CAN transceiver TLE9350VSJ provides a power-save mode. In power-save mode, the power consumption of the TLE9350VSJ is optimized to a minimum

The voltage level on the digital input TxD and the digital output RxD is determined by the power supply level at the V_{10} pin. Depending on the voltage level at the V_{10} pin, the signal levels on the logic pins (STB, TxD and RxD) are compatible with microcontrollers having a 5 V or 3.3 V I/O supply. Usually the digital power supply V_{10} of the transceiver is connected to the I/O power supply of the microcontroller (see **Figure 13**).



5 Modes of operation

The TLE9350VSJ supports the following modes of operation):

- Normal-operating mode
- Power-save mode

The mode selection input pin NEN triggers mode changes. Undervoltage on V_{CC} disables the transmitter output stage. An undervoltage event on the digital supply V_{IO} powers down the device.

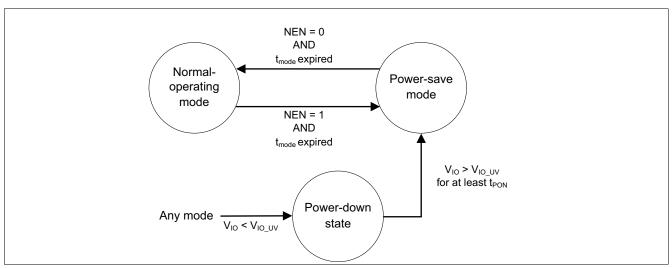


Figure 4 Mode state diagram

5.1 Normal-operating mode

In normal-operating mode all functions of the device are available and the device is fully functional. Data can be received from the HS CAN bus as well as transmitted to the HS CAN bus.

- The transmitter is enabled and drives the serial data stream on the TxD input pin to the bus pins CANH and CANL
- The receiver is enabled and converts the signal from the bus to a serial data stream on the RxD output pin
- · The bus biasing is active
- The TxD time-out function is enabled (see Chapter 6.4)
- The overtemperature protection is enabled (see Chapter 6.6)
- The undervoltage detection on V_{CC} and V_{IO} are enabled (see Chapter 6.3 and Chapter 5.3)

The device enters normal-operating mode by setting the mode selection pin NEN to "low", see **Figure 4**. Normal-operating mode can be entered if the device supply $V_{\rm CC}$ is higher than $V_{\rm CC_UV_R}$. The device enters normal-operating mode after $t_{\rm mode}$ expires.

Note:

If the device recognizes a recessive signal on the TxD input pin during a mode change from any mode to normal-operating mode, then it enables the transmit path after the mode change. If the device recognizes a a dominant signal on the TxD input pin during a mode change to normal-operating mode, then it keeps the transmit path disabled and it blocks the dominant signal in order to not disturb the bus communication. As soon as the device recognizes a recessive signal on the TxD

5.2 Power-save mode

In power-save mode the transmitter and receiver are disabled (see also):

input pin, it enables the transmit path again.



- The transmitter is disabled and the data available on the TxD input is blocked
- The receiver is disabled and the data available on the bus is blocked
- The RxD output pin is permanently set to logical "high"
- The bus biasing is connected to high impedance
- The NEN input pin is active and if set to "low" it changes the mode of operation to normal-operating mode
- The overtemperature protection is disabled
- The undervoltage detection on V_{CC} is disabled. In power-save mode the device can operate without the transmitter supply V_{CC}
- The undervoltage detection on V_{10} is enabled

Power-save mode can be entered from normal-operating mode by setting the NEN pin to logical "high". The device enters this mode after t_{mode} expires or after the period of t_{PON} when coming from power-down state.

5.3 Power-down state

If the supply voltage $V_{\text{IO_UV}}$, then the device powers down independent of the transmitter supply V_{CC} and NEN input pin (see **Figure 5**). In power-down state all functions of the device are disabled and the device is switched off. The input resistors of the receiver are disconnected. The CANH and CANL bus interface of the device is floating and acts as a high impedance input with a very low leakage current. The high impedance input does not influence the recessive level of the CAN and allows an optimized EME performance of the entire network. In power-down state the transceiver is an invisible node to the bus. t_{pon} must expire as a prerequisite for the device to exit power-down state.

- The transmitter and receiver are disabled
- The bus biasing is connected to high impedance
- The TxD time-out function is disabled
- The overtemperature protection is disabled
- The undervoltage detection on V_{CC} is disabled
- The undervoltage detection on V_{10} is enabled

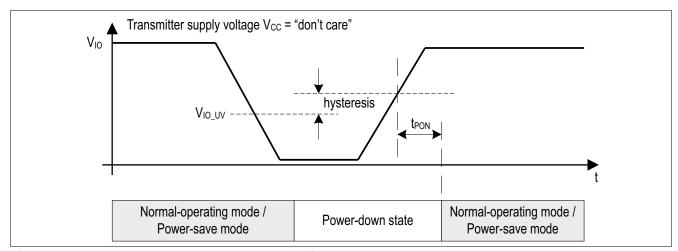


Figure 5 Power-down and power-up behavior and V_{10}



6 Fail safe functions

6.1 Short circuit protection

The CANH and CANL bus outputs are short circuit proof to GND and short circuit proof to a supply voltage. The current limiting circuit is designed to protect the transceiver from damage. If the device heats up due to a continuous short on the CANH or CANL, then the internal overtemperature protection switches off the bus transmitter.

6.2 Unconnected logic pins

All logic input pins have an internal pull-up resistor to V_{10} . If the V_{10} and V_{CC} supply is active and the logical pins are open, the device enters the power-save mode by default.

V_{cc} undervoltage

If the transmitter supply is in undervoltage condition $V_{\rm CC} < V_{\rm CC_UV_F}$, then the device might not be able to provide the correct bus levels on the CANH and CANL output pins. During this time the transmitter is blocked in normal-operating mode, to avoid any interference with the network.

During undervoltage condition $V_{CC} < V_{CC}$ uv $_{F}$, the bus biasing is switched to ground in normal-operating mode.

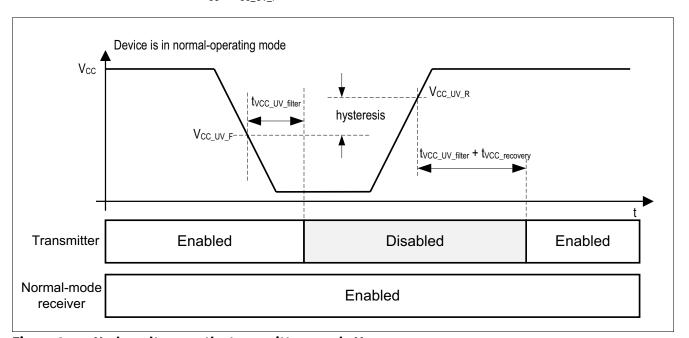


Figure 6 Undervoltage on the transmitter supply V_{cc}

6.4 TxD time-out feature

The TxD time-out feature protects the CAN bus against permanent blocking in case the logical signal on the TxD pin is continuously "low". A continuous "low" signal on the TxD pin might have its root cause in a locked-up microcontroller or in a short circuit on the printed circuit board, for example.

In normal-operating mode, a "low" signal on the TxD pin for the time $t > t_{\mathsf{TxD}}$ enables the TxD time-out feature and the device disables the transmitter (see **Figure 7**). The receiver is still active and the device continues to monitor data on the bus via the RxD output pin.



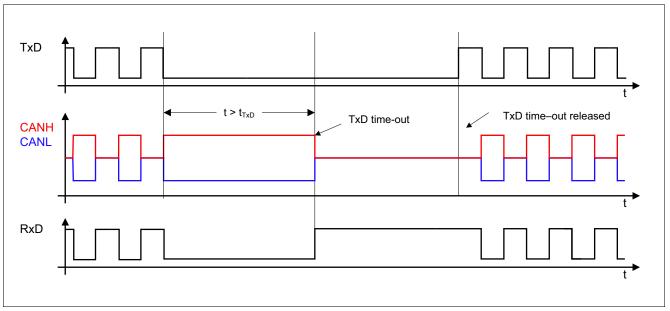


Figure 7 TxD time-out function

Figure 7 shows how the transmitter is deactivated and activated again. A permanent "low" signal on the TxD input pin activates the TxD time-out and deactivates the transmitter. To release the transmitter after a TxD time-out event, the device requires a signal change on the TxD input pin from "low" to "high".

6.5 Delay time for mode change

The device changes the mode of operation within the time window t_{Mode} . During the mode change from power-save mode to non-low power mode the device sets the RxD output "high" permanently, so it does not reflect the status on the CANH and CANL input pins.

After the mode change is completed, the device releases the RxD output pin.

6.6 Overtemperature protection

The TLE9350VSJ has an integrated overtemperature detection, which is designed to protect the device against thermal overstress of the transmitter. The overtemperature protection is only active in normal-operating mode. In case of an overtemperature condition, the temperature sensor disables the transmitter while the transceiver remains in normal-operating mode. After the device cools down it enables the transmitter again (see **Figure 8**). A hysteresis is implemented within the temperature sensor.



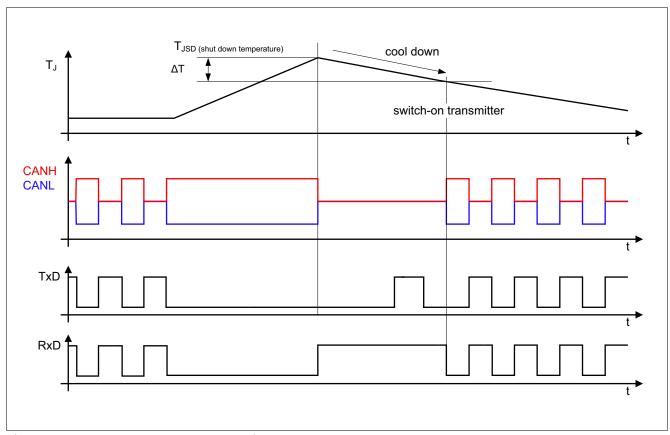


Figure 8 Overtemperature protection



Electrical characteristics 7

7.1 Power supply interface

Electrical characteristics current consumption 7.1.1

Table 5 **Electrical characteristics current consumption**

 $4.75 \text{ V} < V_{CC} < 5.25 \text{ V}; 3.0 \text{ V} < V_{IO} < 5.5 \text{ V}; R_L = 60 \Omega; -40 ^{\circ}\text{C} < T_j < 150 ^{\circ}\text{C}; all voltages with respect to ground; positive to the contraction of t$ current flowing into pin; unless otherwise specified.

Parameter	Symbol		Values	;	Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
Current consumption at $V_{\rm CC}$ normal-operating mode, recessive state	I _{CC_R}	-	1.4	4	mA	$V_{TXD} = V_{IO};$ $V_{NEN} = 0 V;$ $V_{CANH} = V_{CANL} = V_{CC}/2$	P_8.1.1
Current consumption at $V_{\rm CC}$ normal-operating mode, dominant state	I _{CC_D}	_	34	48	mA	$V_{TXD} = V_{NEN} = 0 \; V$	P_8.1.2
Current consumption at V_{10} normal-operating mode	I _{IO}	-	0.9	1.5	mA	$V_{\text{NEN}} = 0 \text{ V};$ $V = V_{\text{IO}};$ $V_{\text{Diff}} = 0 \text{ V};$ recessive	P_8.1.3
Current consumption at V_{CC} power-save mode	I _{CC(PSM)}	-	0.005	5	μΑ	$V_{TXD} = V_{NEN} = V_{IO}$	P_8.1.4
Current consumption at V_{10} power-save mode	I _{IO(PSM)}	-	7	18	μΑ	$V_{\text{TxD}} = V_{\text{NEN}} = V_{\text{IO}};$ 0 V < V_{CC} < 5.5 V	P_8.1.6



7.1.2 Electrical characteristics undervoltage detection

Table 6 Electrical characteristics undervoltage detection

Parameter	Symbol	Values			Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
$V_{\rm CC}$ undervoltage threshold rising edge	$V_{\text{CC_UV_R}}$	3.8	4.2	4.65	V	see Figure 6	P_8.1.11
V _{cc} undervoltage threshold falling edge	V _{CC_UV_F}	3.8	4.2	4.5	V	see Figure 6	P_8.1.21
$\overline{V_{\rm CC}}$ undervoltage filter time	t _{VCC_UV_filter}	4	6	10	μs	²⁾ Figure 6	P_8.1.13
$V_{\rm CC}$ undervoltage recovery time	t _{VCC_recovery}	_	7	70	μs	²⁾ see Figure 6	P_8.1.14
V _{IO} undervoltage threshold	V_{IO_UV}	2.0	2.6	3.0	V	_	P_8.1.15
V _{IO} delay time power-up	t_{PON}	_	40	280	μs	²⁾ see Figure 5	P_8.1.19

¹⁾ V_{CC} undervoltage threshold for rising edge is always higher than undervoltage threshold for falling edge.

²⁾ Not subject to production test, specified by design.



7.2 Electrical characteristics CAN controller interface

Table 7 Electrical characteristics CAN controller interface

Parameter	Symbol		Value	Values		Note or	Number
		Min.	Тур.	Max.		Test Condition	
Receiver output RxD			•		•		
"High" level output current	I _{RxD_H}	-	-2.5	-1	mA	$V_{\text{RxD}} = V_{\text{IO}} - 0.4 \text{ V};$ $V_{\text{Diff}} < 0.5 \text{ V}$	P_8.2.1
"Low" level output current	I _{RxD_L}	1	2.5	-	mA	$V_{\text{RxD}} = 0.4 \text{ V};$ $V_{\text{Diff}} > 0.9 \text{ V}$	P_8.2.2
Transmission input TxD							·
"High" level input voltage	$V_{TxD_{H}}$	0.7 × V ₁₀	_	6.0	V	Recessive state	P_8.2.3
"Low" level input voltage	V_{TxD_L}	-0.3	_	0.3 × V _{IO}	V	Dominant state	P_8.2.4
Internal pull-up resistor TxD	R_{TxD}	35	55	70	kΩ	_	P_8.2.7
Input capacitance	C_{TxD}	-	-	10	pF	1)	P_8.2.8
TxD permanent dominant time-out	t_{TxD}	1	2.3	4	ms	Normal-operating mode	P_8.2.9
non-enable input NEN			•		•		
"High" level input voltage	V_{NEN_H}	0.7 × V ₁₀	_	6.0	V	Power-save mode	P_8.2.13
"Low" level input voltage	V_{NEN_L}	-0.3	-	0.3 × V _{IO}	V	Normal-operating mode	P_8.2.14
Internal pull-up resistor NEN	R _{NEN}	35	55	70	kΩ	_	P_8.2.16
Input capacitance	C _(NEN)	-	_	10	pF	1)	P_8.2.20

¹⁾ Not subject to production test, specified by design.



Electrical characteristics receiver 7.3

Electrical characteristics receiver

 $4.75 \text{ V} < V_{CC} < 5.25 \text{ V}; 3.0 \text{ V} < V_{IO} < 5.5 \text{ V}; R_L = 60 \Omega; -40 ^{\circ}\text{C} < T_i < 150 ^{\circ}\text{C}; all voltages with respect to ground; positive to gr$ current flowing into pin; unless otherwise specified.

Parameter	Symbol		Value	s	Unit	Note or Test Condition	Number
		Min.	Тур.	Max.			
Differential range dominant normal-operating mode	V _{Diff_D_Range}	0.9	_	8.0	V	$^{1)}$ -12 V $\leq V_{\text{CMR}} \leq 12 \text{ V}$	P_8.3.3
Differential range recessive normal-operating mode	V _{Diff_R_Range}	-3.0	_	0.5	V	$^{1)}$ -12V $\leq V_{\rm CMR} \leq 12$ V	P_8.3.5
Common mode range	CMR	-12	_	12	V	-	P_8.3.11
Single ended internal resistance	R_{CAN_H}, R_{CAN_L}	6	40	50	kΩ	1) recessive state; $-2 \text{ V} \le V_{\text{CANH}} \le 7 \text{ V};$ $-2 \text{ V} \le V_{\text{CANL}} \le 7 \text{ V}$	P_8.3.12
Differential internal resistance	R_{Diff}	12	80	100	kΩ	1) recessive state; $-2 \text{ V} \le V_{\text{CANH}} \le 7 \text{ V};$ $-2 \text{ V} \le V_{\text{CANL}} \le 7 \text{ V}$	P_8.3.14
Input resistance deviation between CANH and CANL	ΔR _i	-3	_	3	%	¹⁾ recessive state; $V_{\text{CANH}} = V_{\text{CANL}} = 5 \text{ V}$	P_8.3.16
Input capacitance CANH, CANL versus GND	C _{In}	_	_	40	pF	1)2) recessive state; normal-operating mode	P_8.3.17
Differential input capacitance	C _{InDiff}	_	4	20	pF	1)2) recessive state; normal-operating mode	P_8.3.18

¹⁾ Not subject to production test, specified by design.

²⁾ S2P-Method; f = 10 MHz.



7.4 Electrical characteristics transmitter

Table 9 Electrical characteristics transmitter

Parameter	Symbol		Value	S	Unit	Note or	Number
		Min.	Тур.	Мах.		Test Condition	
CANL, CANH recessive output voltage normal-operating mode	$V_{CANL,H}$	2.0	2.5	3.0	V	V _{TxD} = V _{IO} ; no load	P_8.4.1
CANH, CANL recessive output voltage difference normal-operating mode	$V_{\text{Diff}_{R_NM}} = V_{\text{CANH}} - V_{\text{CANL}}$	-500	-10	50	mV	$V_{TXD} = V_{IO};$ no load	P_8.4.2
CANL dominant output voltage normal-operating mode	V_{CANL}	0.5	1.5	2.25	V	$V_{TXD} = 0 \; V;$ $50 \; \Omega < R_{L} < 65 \; \Omega$	P_8.4.3
CANH dominant output voltage normal-operating mode	V_{CANH}	2.75	3.4	4.5	V	$V_{TXD} = 0 \; V;$ $50 \; \Omega < R_{L} < 65 \; \Omega$	P_8.4.4
Differential voltage dominant normal-operating mode $V_{\text{Diff}} = V_{\text{CANH}} - V_{\text{CANL}}$	$V_{\mathrm{Diff_D_NM}}$	1.5	1.9	2.5	V	$V_{\text{TXD}} = 0 \text{ V};$ $50 \Omega < R_{\text{L}} < 65 \Omega$	P_8.4.5
Differential voltage dominant extended bus load normal-operating mode	$V_{Diff_EXT_BL}$	1.4	1.9	3.3	V	$V_{\text{TXD}} = 0 \text{ V};$ 45 $\Omega < R_{\text{L}} < 70 \Omega$	P_8.4.6
Differential voltage dominant high extended bus load normal-operating mode	V _{Diff_HEXT_BL}	1.5	3.5	5.0	V	$V_{\text{TxD}} = 0 \text{ V};$ $R_{\text{L}} = 2240\Omega;$ static behavior	P_8.4.7
Driver symmetry ($V_{\text{SYM}} = V_{\text{CANH}} + V_{\text{CANL}}$)	V_{SYM}	0.9 × V _{cc}	1.0 × V _{cc}	1.1 × V _{CC}	V	^{1) 2)} C ₁ = 4.7 nF	P_8.4.10
CANL short circuit current	I _{CANLsc}	-115	90	115	mA	$^{1)}$ -3 $V < V_{CANLshort} < 18 V;$ $t < t_{TXD};$ $V_{TXD} = 0 V$	P_8.4.11
CANL short circuit current	I _{CANLsc2}	40	90	115	mA	$V_{\text{CANLshort}} = 18 \text{ V};$ $t < t_{\text{TxD}};$ $V_{\text{TxD}} = 0 \text{ V}$	P_8.4.23
CANH short circuit current	I _{CANHsc}	-115	-90	115	mA	$^{1)}$ -3 V < $V_{\text{CANHshort}}$ = 18 V; $t < t_{\text{TxD}}$; V_{TxD} = 0 V	P_8.4.13
CANH short circuit current	I _{CANHsc2}	-115	-90	-40	mA	$V_{\text{CANHshort}} = -3 \text{ V};$ $t < t_{\text{TxD}};$ $V_{\text{TxD}} = 0 \text{ V}$	P_8.4.24
Leakage current, CANH	I _{CANH,lk}	-5	1	5	μΑ	$V_{CC} = V_{IO} = 0 \text{ V};$ $0 \text{ V} < V_{CANH} \le 5 \text{ V};$ $V_{CANH} = V_{CANL};$	P_8.4.19



Table 9 Electrical characteristics transmitter (Continued)

Parameter	Symbol	Values			Unit	Note or	Number	
		Min. Typ.		Max.		Test Condition		
Leakage current, CANL	I _{CANL,Ik}	-5	1	5	μΑ	$V_{\text{CC}} = V_{\text{IO}} = 0 \text{ V};$ $0 \text{ V} < V_{\text{CANL}} \le 5 \text{ V};$ $V_{\text{CANH}} = V_{\text{CANL}}$	P_8.4.20	
CANH, CANL output voltage difference slope, recessive to dominant	V _{diff_slope_rd}	-	42	70	V/µs	$^{1)}$ 30% to 70% of measured differential bus voltage, C_2 = 100 pF, R_L = 60 Ω , 4.75 V < V_{CC} < 5.25 V	P_8.4.21	
CANH, CANL output voltage difference slope, dominant to recessive	$V_{ m diff_slope_dr}$	-	42	70	V/µs	$^{1)}$ 70% to 30% of measured differential bus voltage, $C_2 = 100 \text{ pF}, R_L = 60 \Omega,$ 4.75 V < V_{CC} < 5.25 V	P_8.4.22	

¹⁾ Not subject to production test, specified by design.

²⁾ V_{SYM} is observed during dominant and recessive state and also during the transition from dominant to recessive state and vice versa, while TxD is stimulated by a square wave signal with a frequency of 1 MHz.



7.5 Electrical characteristics dynamic transceiver parameters

Table 10 Electrical characteristics dynamic transceiver parameters

Parameter	Symbol	Values			Unit	Note or	Number	
		Min.	Тур.	Max.		Test Condition		
Propagation delay TxD-to-RxD	t _{Loop}	80	150	255	ns	$C_1 = 0 \text{ pF},$ $C_2 = 100 \text{ pF},$ $C_{RXD} = 15 \text{ pF};$ (see Figure 10)	P_8.5.1	
Propagation delay increased load TxD-to-RxD	t _{Loop_150}	80	180	330	ns	$C_1 = 0 \text{ pF},$ $C_2 = 100 \text{ pF},$ $C_{RXD} = 15 \text{ pF},$ $R_L = 150 \Omega^{-1}$	P_8.5.2	
Propagation delay TxD to bus "low" to dominant	$t_{d(L)_{L}T}$	30	70	140	ns	$C_1 = 0 \text{ pF},$ $C_2 = 100 \text{ pF},$ $C_{RXD} = 15 \text{ pF};$ (see Figure 10)	P_8.5.3	
Propagation delay TxD to bus "high" to recessive	$t_{d(H)_{T}}$	30	90	140	ns	$C_1 = 0 \text{ pF},$ $C_2 = 100 \text{ pF},$ $C_{RXD} = 15 \text{ pF};$ (see Figure 10)	P_8.5.4	
Propagation delay bus to RxD dominant to "low"	$t_{d(L)_{-}R}$	30	90	140	ns	$C_{\text{RxD}} = 15 \text{ pF},$ Independent of t_{Bit} ; (see Figure 10)	P_8.5.5	
Propagation delay bus to RxD recessive to "high"	t _{d(H)_R}	30	100	140	ns	$C_{\text{RxD}} = 15 \text{ pF},$ Independent of t_{Bit} ; (see Figure 10)	P_8.5.6	
Delay Times	1	l .					1	
Delay time for mode change	t_{Mode}	-	12	20	μs	1)	P_8.5.7	
Hold-up time of power-save mode	t_{Hold_PS}	180	-	-	μs	²⁾ see Figure 12	P_8.5.19	
CAN FD characteristics								
Received recessive bit width at 2 MBit/s	t _{Bit(RxD)_2M}	420	450	520	ns	$C_2 = 100 \text{ pF};$ $C_{RXD} = 15 \text{ pF};$ $t_{Bit} = 500 \text{ ns};$ see Figure 11	P_8.5.13	
Received recessive bit width at 5 MBit/s	t _{Bit(RxD)_5M}	120	150	220	ns	$C_2 = 100 \text{ pF};$ $C_{RXD} = 15 \text{ pF};$ $t_{Bit} = 200 \text{ ns};$ see Figure 11	P_8.5.14	



Table 10 Electrical characteristics dynamic transceiver parameters (Continued)

Parameter	Symbol	Values			Unit	Note or	Number
		Min.	Тур.	Max.		Test Condition	
Transmitted recessive bit width at 2 MBit/s	t _{Bit(Bus)_2M}	455	470	510	ns	$C_2 = 100 \text{ pF};$ $C_{RXD} = 15 \text{ pF};$ $t_{Bit} = 500 \text{ ns};$ see Figure 11	P_8.5.15
Transmitted recessive bit width at 5 MBit/s	t _{Bit(Bus)_5M}	155	170	210	ns	$C_2 = 100 \text{ pF};$ $C_{RXD} = 15 \text{ pF};$ $t_{Bit} = 200 \text{ ns};$ see Figure 11	P_8.5.16
Receiver timing symmetry at 2 MBit/s $\Delta t_{\text{Rec}_2M} = t_{\text{Bit}(\text{RxD})_2M} - t_{\text{Bit}(\text{Bus})_2M}$	$\Delta t_{ m Rec_2M}$	-45	-23	15	ns	$C_2 = 100 \text{ pF};$ $C_{RXD} = 15 \text{ pF};$ $t_{Bit} = 500 \text{ ns};$ see Figure 11	P_8.5.17
Receiver timing symmetry at 5 MBit/s $\Delta t_{\text{Rec}_5M} = t_{\text{Bit}(\text{RxD})_5M} - t_{\text{Bit}(\text{Bus})_5M}$	$\Delta t_{ m Rec_5M}$	-45	-23	15	ns	$C_2 = 100 \text{ pF};$ $C_{RXD} = 15 \text{ pF};$ $t_{Bit} = 200 \text{ ns};$ see Figure 11	P_8.5.18

¹⁾ Not subject to production test, specified by design.

²⁾ In case of mode transition from normal-operating to power-save and back to normal-operating, the transceiver is recommended to stay for minimum of 200 μ s in the power-save mode to be in the safe operating area; to receive and transmit CAN messages properly.



Diagrams 7.6

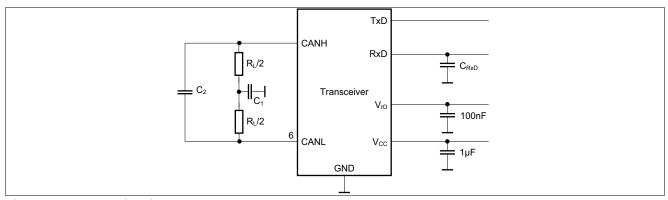


Figure 9 **Test circuit**

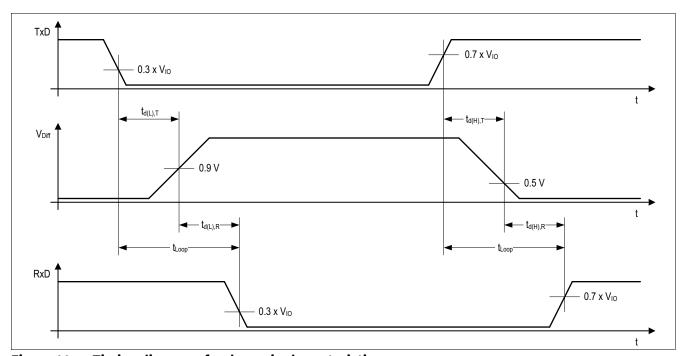
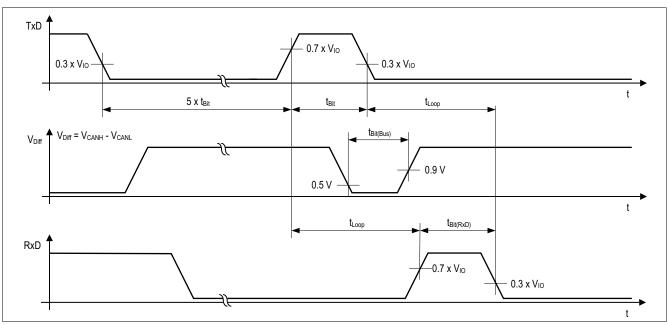


Figure 10 Timing diagrams for dynamic characteristics





Recessive bit time for five dominant bits followed by one recessive bit Figure 11

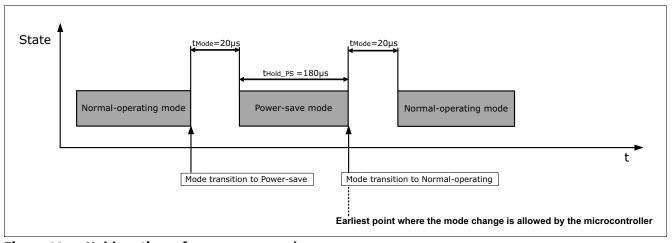


Figure 12 Hold-up time of power-save mode



8 Application information

8.1 ESD robustness according to IEC 61000-4-2

Tests for ESD robustness according to IEC 61000-4-2 Gun test (150 pF, 330 Ω) have been performed. The results and test conditions are available in a separate test report.

Table 11 ESD robustness according to IEC 61000-4-2

Performed test	Result	Unit	Remarks
Electrostatic discharge voltage at pin CANH and CANL versus GND	≥ +8	kV	1) positive pulse
Electrostatic discharge voltage at pin CANH and CANL versus GND	≤ -8	kV	1) negative pulse

Not subject to production test. ESD susceptibility "ESD GUN" according to GIFT/ICT paper: "EMC Evaluation of CAN Transceivers, version IEC TS62228", section 4.3. (DIN EN61000-4-2).
 Tested by external test facility (IBEE Zwickau).

8.2 Application example

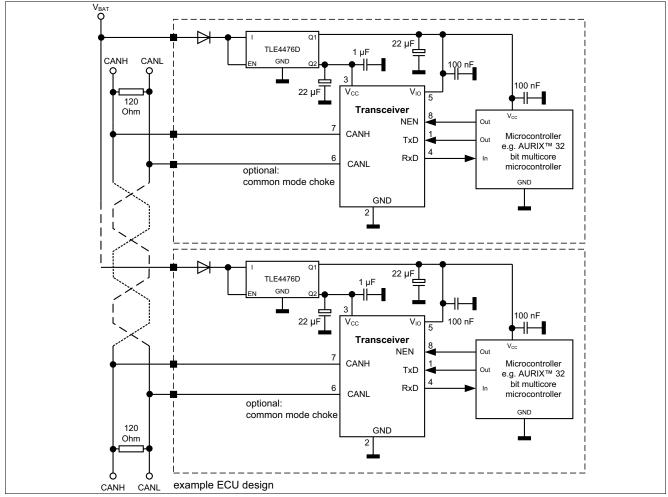


Figure 13 Application circuit



8.3 Voltage adaption to the microcontroller supply

To adapt the digital input and output levels of the device to the I/O levels of the microcontroller, connect the power supply pin V_{IO} to the microcontroller voltage supply, see **Figure 13**.

Note:

If case no dedicated digital supply voltage V_{IO} is required in the application, then connect the digital supply voltage V_{IO} to the transmitter supply V_{CC} .

8.4 Further application information

For further information you may visit: https://www.infineon.com/automotive-transceiver



9 Package information

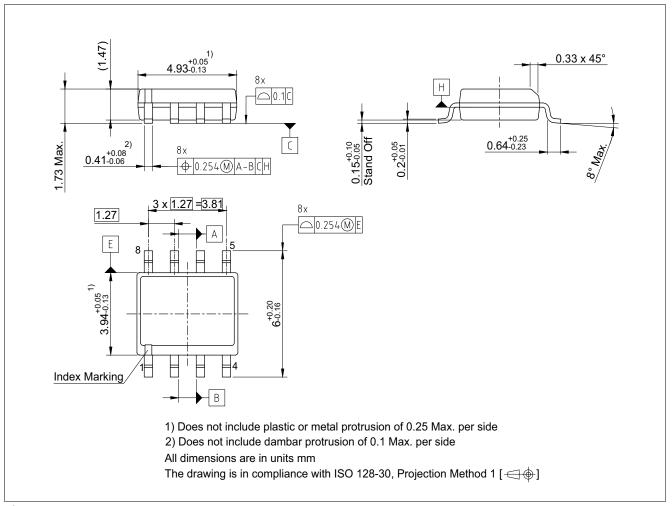


Figure 14 PG-DSO-8

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e. Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Further information on packages

https://www.infineon.com/packages



10 Revision history

Revision	Date	Changes
1.2	2022-03-18	Added new parameter P_8.5.19
		Editorial changes
1.1	2021-07-30	Minimum value for Parameter P_8.1.13 V _{CC} undervoltage filter time specified
		• $V_{\rm CC}$ undervoltage threshold (P_8.1.11 and P_8.1.21) for rising and falling edge specified
		• Updated description of V _{CC} undervoltage detection
		Added new parameter P_8.4.23 and P_8.4.24
		Updated figure of application example
1.0	2020-11-06	Datasheet created

Trademarks

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